# P-Channel Enhancement Mode Field Effect Transistor

## Product Summary

- $V_{DS}$ -60 V
- $I_D$ -100 A
- $R_{DS(ON)}$( at $V_{GS}$=-10V) 8.8mΩ
- $R_{DS(ON)}$( at $V_{GS}$=-6V) 10mΩ
- 100% EAS Tested
- 100% $V_{DS}$ Tested

## General Description

- Split gate trench MOSFET technology
- High density cell design for low $R_{DS(ON)}$
- Excellent stability and uniformityera(ty06.34 T9(r)13(m)-6(6.04 842.04

■ **Electrical Characteristics** ($T_J$=25 unless otherwise noted)

## Typical Electrical and Thermal Characteristics Diagrams

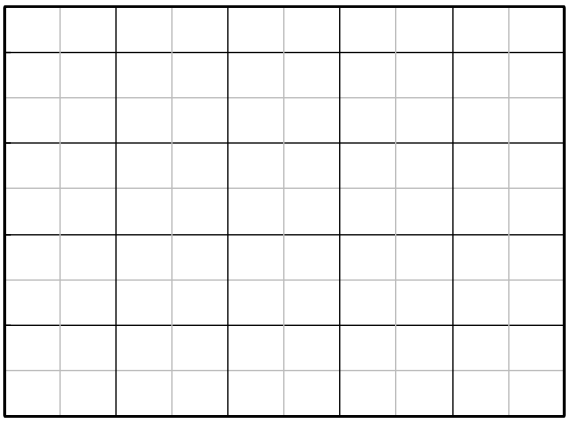

Figure 1. Output Characteristics

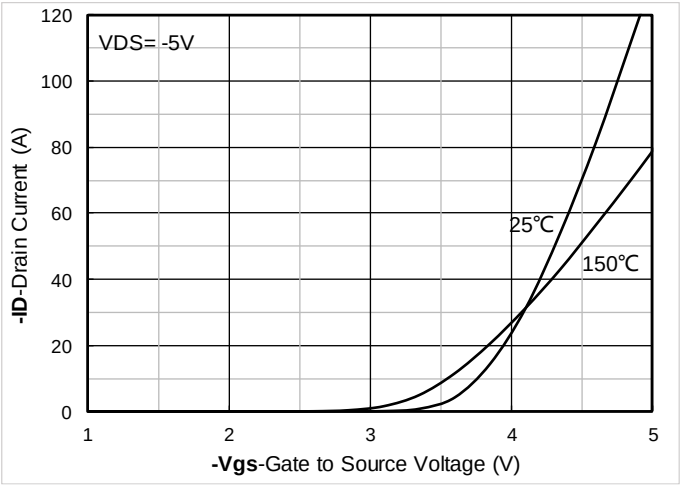


Figure 2. Transfer Characteristics

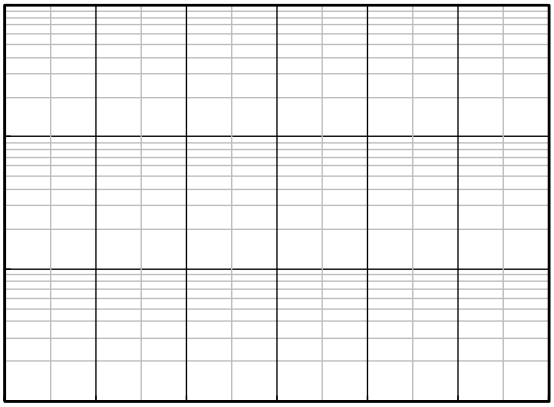

Figure 3. Capacitance Characteristics

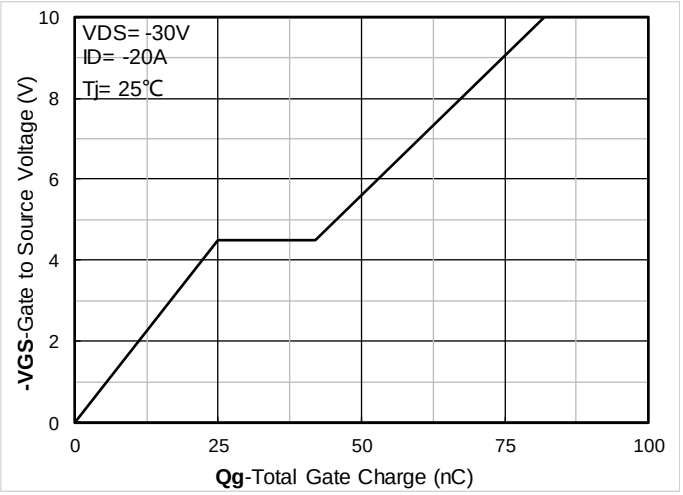


Figure 4. Gate Charge

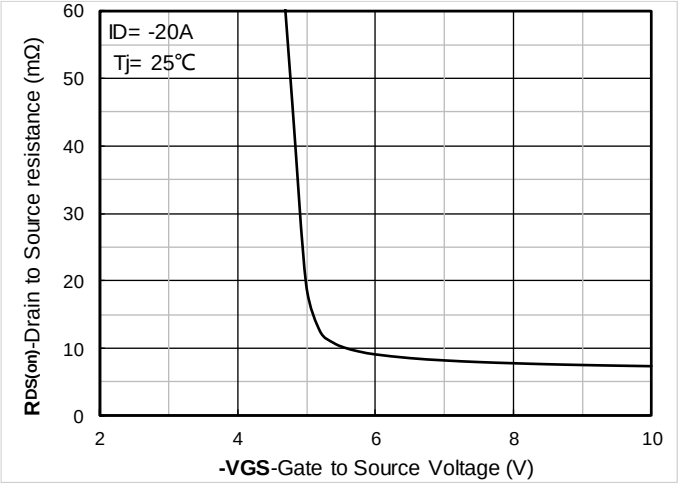


Figure 5. On-Resistance vs Gate to Source Voltage

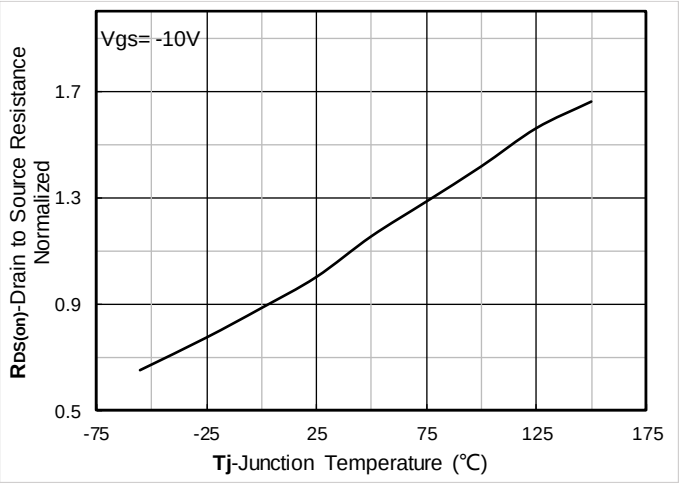


Figure 6. Normalized On-Resistance

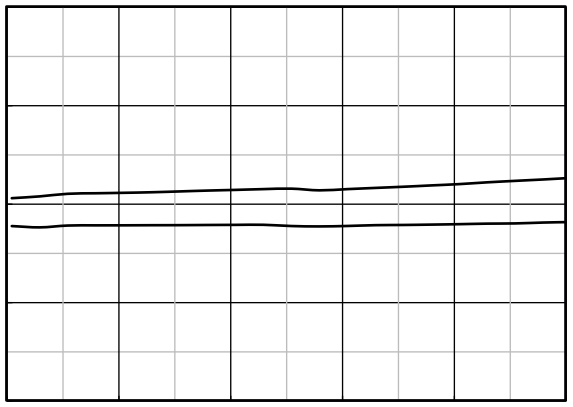

Figure 7. $R_{DS(on)}$ VS Drain Current

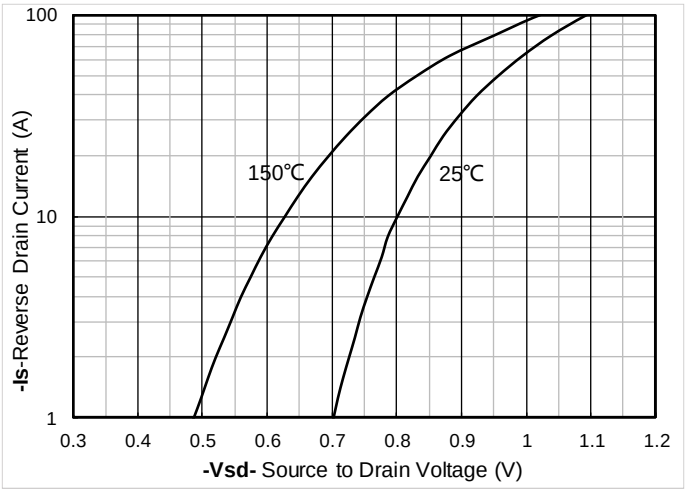


Figure 8. Forward characteristics of reverse diode

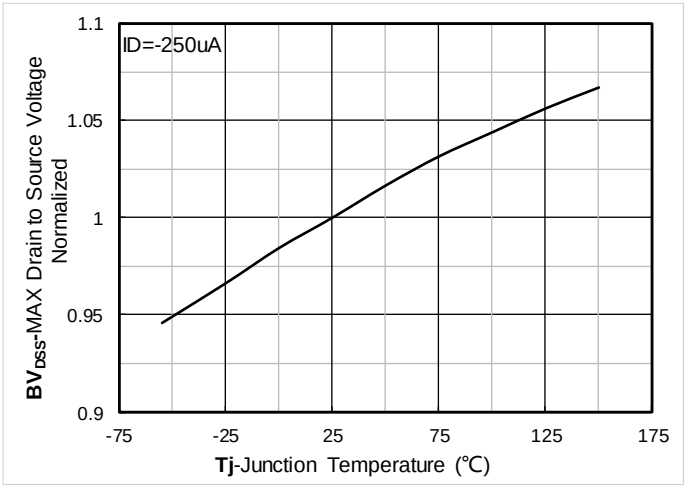


Figure 9. Normalized breakdown voltage

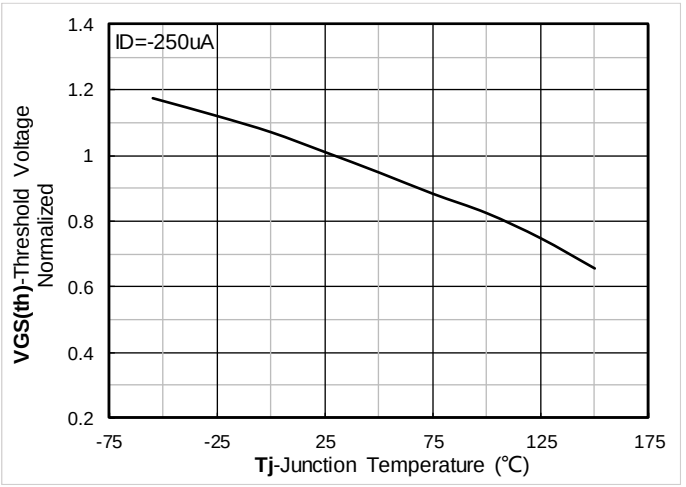


Figure 10. Normalized Threshold voltage

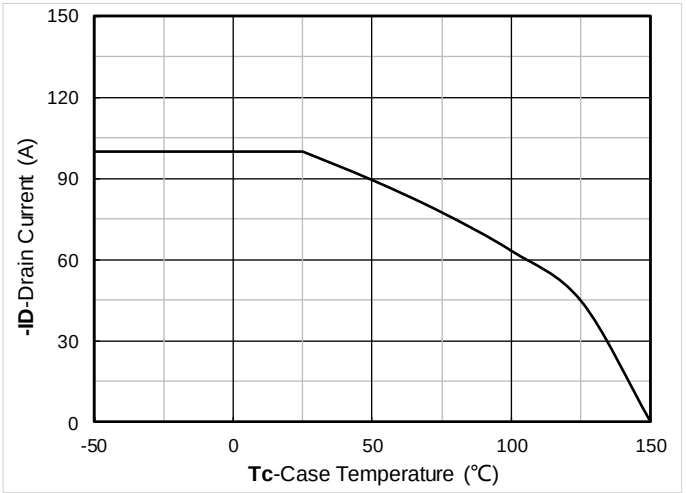


Figure 11. Current dissipation

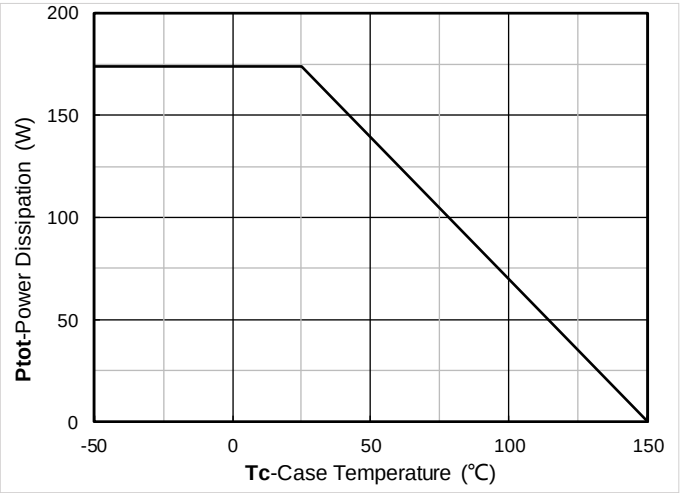


Figure 12. Power dissipation

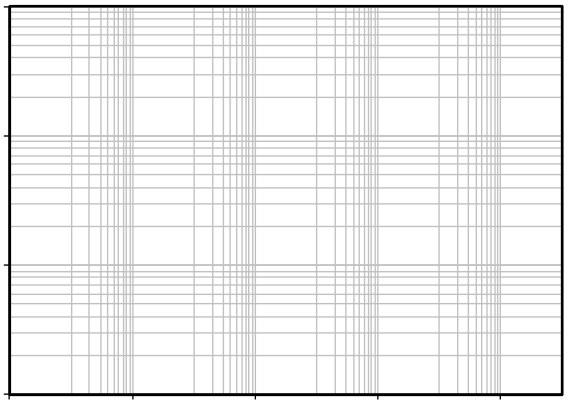

Figure 13. Maximum Transient Thermal Impedance



Figure 14. Safe Operation Area

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## Disclaimer

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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on it 9 Tf1 0 0 1 32.64 654.94W*nBT/ReS(o)-3(n)-3(e)-3( )-41(o)9(n)-3( )-41(i)-4(t 9 Tf1 0 0 1 32.64 654.94W*nBT